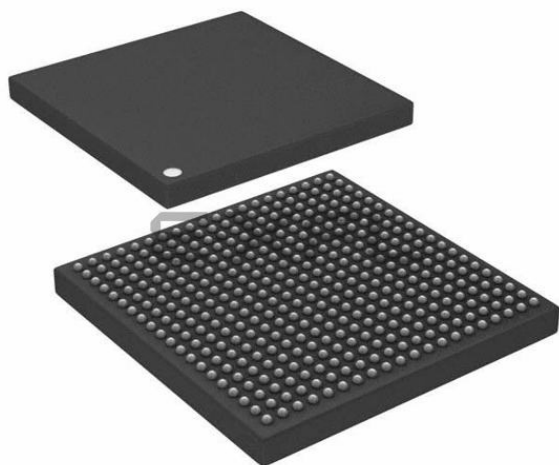




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Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of [Embedded - Microprocessors](#)

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Active
Core Processor	ARM1136JF-S
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	532MHz
Co-Processors/DSP	Multimedia; GPU, IPU, VFP
RAM Controllers	LPDDR, DDR2
Graphics Acceleration	Yes
Display & Interface Controllers	Keypad, KPP, LCD
Ethernet	10/100Mbps (1)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	1.8V, 2.0V, 2.5V, 2.7V, 3.0V, 3.3V
Operating Temperature	-20°C ~ 70°C (TA)
Security Features	Secure Fusebox, Secure JTAG, Tamper Detection
Package / Case	400-LFBGA
Supplier Device Package	400-LFBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx357djq5cr2

- PWM
- SPDIF transceiver
- 3 UART (up to 4.0 Mbps each)

1.2 Ordering Information

Table 1 provides the ordering information for the i.MX35 processors for consumer and industrial applications.

Table 1. Ordering Information

Description	Part Number	Silicon Revision	Package ¹	Speed	Operating Temperature Range (°C)	Signal Ball Map Locations	Ball Map
i.MX353	MCIMX353CVM5B	2.0	5284	532 MHz	–40 to 85	Table 94	Table 96
i.MX353	MCIMX353DVM5B	2.0	5284	532 MHz	–20 to 70	Table 94	Table 96
i.MX357	MCIMX357CVM5B	2.0	5284	532 MHz	–40 to 85	Table 94	Table 96
i.MX357	MCIMX357DVM5B	2.0	5284	532 MHz	–20 to 70	Table 94	Table 96
i.MX353	MCIMX353CJQ5C	2.1	5284	532MHz	-40 to 85	Table 95	Table 97
i.MX353	MCIMX353DJQ5C	2.1	5284	532MHz	-20 to 70	Table 95	Table 97
i.MX357	MCIMX357CJQ5C	2.1	5284	532MHz	-40 to 85	Table 95	Table 97
i.MX357	MCIMX357DJQ5C	2.1	5284	532MHz	-20 to 70	Table 95	Table 97

¹ Case 5284 is RoHS-compliant, lead-free, MSL = 3, 1.

The ball map for silicon revision 2.1 is different than the ballmap for silicon revision 2.0. The layout for each revision is not compatible, so it is important that the correct ballmap be used to implement the layout. See Section 5, “Package Information and Pinout.”

Table 2 shows the functional differences between the different parts in the i.MX35 family.

Table 2. Functional Differences in the i.MX35 Parts

Module	MCIMX351	MCIMX353	MCIMX355	MCIMX356	MCIMX357
I2C (3)	Yes	Yes	Yes	Yes	Yes
CSPI (2)	Yes	Yes	Yes	Yes	Yes
SSI/I2S (2)	Yes	Yes	Yes	Yes	Yes
ESAI	Yes	Yes	Yes	Yes	Yes
SPDIF I/O	Yes	Yes	Yes	Yes	Yes
USB HS Host	Yes	Yes	Yes	Yes	Yes
USB OTG	Yes	Yes	Yes	Yes	Yes
FlexCAN (2)	Yes	Yes	Yes	Yes	Yes
MLB	Yes	Yes	Yes	Yes	Yes

Table 2. Functional Differences in the i.MX35 Parts (continued)

Module	MCIMX351	MCIMX353	MCIMX355	MCIMX356	MCIMX357
Ethernet	Yes	Yes	Yes	Yes	Yes
1-Wire	Yes	Yes	Yes	Yes	Yes
KPP	Yes	Yes	Yes	Yes	Yes
SDIO/MMC (2)	Yes	Yes	Yes	Yes	Yes
SDIO/Memory Stick	Yes	Yes	Yes	Yes	Yes
External Memory Controller (EMC)	Yes	Yes	Yes	Yes	Yes
JTAG	Yes	Yes	Yes	Yes	Yes
PATA	—	Yes	Yes	Yes	Yes
CE-ATA	—	Yes	Yes	Yes	Yes
Image Processing Unit (IPU) (inversion and rotation, pre- and post-processing, camera interface, blending, display controller)	—	Yes	Yes	Yes	Yes
Open VG graphics acceleration (GPU)	—	Yes	—	Yes	Yes

Table 4. Digital and Analog Modules (continued)

Block Mnemonic	Block Name	Domain ¹	Subsystem	Brief Description
ESAI	Enhanced serial audio interface	SDMA	Connectivity peripherals	The enhanced serial audio interface (ESAI) provides a full-duplex serial port for serial communication with a variety of serial devices, including industry-standard codecs, SPDIF transceivers, and other DSPs. The ESAI consists of independent transmitter and receiver sections, each section with its own clock generator.
eSDHCv2 (3)	Enhanced secure digital host controller	ARM	Connectivity peripherals	The eSDHCv2 consists of four main modules: CE-ATA, MMC, SD and SDIO. CE-ATA is a hard drive interface that is optimized for embedded applications of storage. The MultiMediaCard (MMC) is a universal, low-cost, data storage and communication media to applications such as electronic toys, organizers, PDAs, and smart phones. The secure digital (SD) card is an evolution of MMC and is specifically designed to meet the security, capacity, performance, and environment requirements inherent in emerging audio and video consumer electronic devices. SD cards are categorized into Memory and I/O. A memory card enables a copyright protection mechanism that complies with the SDMI security standard. SDIO cards provide high-speed data I/O (such as wireless LAN via SDIO interface) with low power consumption. Note: CE-ATA is not available for the MCIMX351.
FEC	Ethernet	SDMA	Connectivity peripherals	The Ethernet media access controller (MAC) is designed to support both 10 and 100 Mbps Ethernet/IEEE 802.3 networks. An external transceiver interface and transceiver function are required to complete the interface to the media
GPIO(3)	General purpose I/O modules	ARM	Pins	Used for general purpose input/output to external ICs. Each GPIO module supports 32 bits of I/O.
GPT	General purpose timers	ARM	Timer peripherals	Each GPT is a 32-bit free-running or set-and-forget mode timer with a programmable prescaler and compare and capture registers. A timer counter value can be captured using an external event and can be configured to trigger a capture event on either the leading or trailing edges of an input pulse. When the timer is configured to operate in set-and-forget mode, it is capable of providing precise interrupts at regular intervals with minimal processor intervention. The counter has output compare logic to provide the status and interrupt at comparison. This timer can be configured to run either on an external clock or on an internal clock.
GPU2D	Graphics processing unit 2Dv1	ARM	Multimedia peripherals	This module accelerates OpenVG and GDI graphics. Note: Not available for the MCIMX351.

Table 14 shows the DC electrical characteristics for GPIO, DDR2, mobile DDR, and SDRAM pins. The term NVCC refers to the power supply voltage that feeds the I/O of the module in question. For example, NVCC for the SD/MMC interface refers to NVCC_SDIO.

Table 14. I/O Pin DC Electrical Characteristics

Pin	DC Electrical Characteristics	Symbol	Test Condition	Min.	Typ.	Max.	Unit
GPIO	High-level output voltage	Voh	Ioh = -1 mA Ioh = specified drive	NVCC - 0.15 0.8 × NVCC	—	—	V
	Low-level output voltage	Vol	Iol = 1 mA Iol = specified drive	—	—	0.15 0.2 × NVCC	V
	High-level output current for slow mode (Voh = 0.8 × NVCC)	Ioh	Standard drive High drive Max. drive	-2.0 -4.0 -8.0	—	—	mA
	High-level output current for fast mode (Voh = 0.8 × NVCC)	Ioh	Standard drive High drive Max. drive	-4.0 -6.0 -8.0	—	—	mA
	Low-level output current for slow mode (Voh = 0.2 × NVCC)	Iol	Standard drive High drive Max. drive	2.0 4.0 8.0	—	—	mA
	Low-level output current for fast mode (Voh = 0.2 × NVCC)	Iol	Standard drive High drive Max. drive	4.0 6.0 8.0	—	—	mA
	High-level DC Input Voltage with 1.8 V, 3.3 V NVCC (for digital cells in input mode)	VIH	—	0.7 × NVCC	—	NVCC	V
	Low-level DC Input Voltage with 1.8 V, 3.3 V NVCC (for digital cells in input mode)	VIL	—	-0.3 V	—	0.3 × NVCC	V
	Input Hysteresis	VHYS	OVDD = 3.3 V OVDD = 1.8 V	—	410 330	—	mV
	Schmitt trigger VT+	VT+	—	0.5 × NVCC	—	—	V
	Schmitt trigger VT-	VT-	—	—	—	0.5 × NVCC	V
	Pull-up resistor (22 kΩ PU)	Rpu	Vi = 0	—	22	—	kΩ
	Pull-up resistor (47 kΩ PU)	Rpu	Vi = 0	—	47	—	kΩ
	Pull-up resistor (100 kΩ PU)	Rpu	Vi = 0	—	100	—	kΩ
	Pull-down resistor (100 kΩ PD)	Rpd	Vi = NVCC	—	100	—	kΩ
	External resistance to pull keeper up when enabled	Rkpu	Ipu > 620 μA @ min Vddio = 3.0 V	—	—	4.8	kΩ
	External resistance to pull keeper down when enabled	Rkpd	Ipu > 510 μA @ min Vddio = 3.0 V	—	—	5.9	kΩ

Table 14. I/O Pin DC Electrical Characteristics (continued)

Pin	DC Electrical Characteristics	Symbol	Test Condition	Min.	Typ.	Max.	Unit
DDR2	High-level output voltage	V _{oh}	—	NVCC – 0.28	—	—	V
	Low-level output voltage	V _{ol}	—	—	—	0.28	V
	Output min. source current	I _{oh}	—	–13.4	—	—	mA
	Output min. sink current	I _{ol}	—	13.4	—	—	mA
	DC input logic high	V _{IH} (dc)	—	$NVCC \div 2 + 0.125$	—	NVCC + 0.3	V
	DC input logic low	V _{IL} (dc)	—	–0.3 V	—	$NVCC \div 2 - 0.125$	V
	DC input signal voltage (for differential signal)	V _{in} (dc)	—	–0.3	—	NVCC + 0.3	V
	DC differential input voltage	V _{id} (dc)	—	0.25	—	NVCC + 0.6	V
	Termination voltage	V _{tt}	—	$NVCC \div 2 - 0.04$	NVCC $\div 2$	$NVCC \div 2 + 0.04$	V
	Input current (no pull-up/down)	I _{IN}	—	—	—	±1	μA
	Tri-state I/O supply current	I _{cc} – N VCC	—	—	—	±1	μA
Mobile DDR	High-level output voltage	—	I _{OH} = –1mA I _{OH} = specified drive	$NVCC - 0.08$ $0.8 \times NVCC$	—	—	V
	Low-level output voltage	—	I _{OL} = 1mA I _{OL} = specified drive	—	—	0.08 $0.2 \times NVCC$	V
	High-level output current (V _{oh} = 0.8 × NVCCV)	—	Standard drive High drive Max. drive	–3.6 –7.2 –10.8	—	—	mA
	Low-level output current (V _{ol} = 0.2 × NVCCV)	—	Standard Drive High Drive Max. Drive	3.6 7.2 10.8	—	—	mA
	High-Level DC CMOS input voltage	V _{IH}	—	0.7 × NVCC	—	NVCC + 0.3	V
	Low-Level DC CMOS input voltage	V _{IL}	—	–0.3	—	0.2 × NVCC	V
	Differential receiver V _{TH} +	V _{TH} +	—	—	—	100	mV
	Differential receiver V _{TH} –	V _{TH} –	—	–100	—	—	mV
	Input current (no pull-up/down)	I _{IN}	V _I = 0 V _I = NVCC	—	—	±1	μA
	Tri-state I/O supply current	I _{cc} – N VCC	V _I = NVCC or 0	—	—	±1	μA

Table 19. AC Electrical Characteristics, GPIO Pins in Fast Slew Rate Mode
[NVCC = 1.65 V–1.95 V]

Parameter	Symbol	Test Condition	Min. Rise/Fall	Typ.	Max. Rise/Fall	Units
Duty cycle	Fduty	—	40	—	60	%
Output pin slew rate (max. drive)	tps	25 pF 50 pF	0.40/0.57 0.25/0.36	0.72/0.97 0.43/0.61	1.2/1.5 0.72/0.95	V/ns
Output pin slew rate (high drive)	tps	25 pF 50 pF	0.38/0.48 0.20/0.30	0.59/0.81 0.34/0.50	0.98/1.27 0.56/0.72	V/ns
Output pin slew rate (standard drive)	tps	25 pF 50 pF	0.23/0.32 0.13/0.20	0.40/0.55 0.23/0.34	0.66/0.87 0.38/0.52	V/ns
Output pin di/dt (max. drive)	tdit	25 pF 50 pF	7 7	43 46	112 118	mA/ns
Output pin di/dt (high drive)	tdit	25 pF 50 pF	11 12	31 33	81 85	mA/ns
Output pin di/dt (standard drive)	tdit	25 pF 50 pF	9 10	27 28	71 74	mA/ns

Table 20. AC Electrical Characteristics of GPIO Pins in Slow Slew Rate Mode
[NVCC = 2.25 V–2.75 V]

Parameter	Symbol	Test Condition	Min. Rise/Fall	Typ.	Max. Rise/Fall	Units
Duty cycle	Fduty	—	40	—	60	%
Output pin slew rate (max. drive)	tps	25 pF 40 pF 50 pF	0.63/0.85 0.52/0.67 0.41/0.59	1.10/1.40 0.90/1.10 0.73/0.99	1.86/2.20 1.53/1.73 1.20/1.50	V/ns
Output pin slew rate (high drive)	tps	25 pF 40 pF 50 pF	0.40/0.58 0.33/0.43 0.25/0.37	0.71/0.98 0.56/0.70 0.43/0.60	1.16/1.40 0.93/1.07 0.68/0.90	V/ns
Output pin slew rate (standard drive)	tps	25 pF 40 pF 50 pF	0.24/0.36 0.19/0.25 0.13/0.21	0.41/0.59 0.32/0.35 0.23/0.33	0.66/0.87 0.51/0.59 0.36/0.48	V/ns
Output pin di/dt (max. drive)	tdit	25 pF 50 pF	22 23	62 65	148 151	mA/ns
Output pin di/dt (high drive)	tdit	25 pF 50 pF	15 16	42 44	102 107	mA/ns
Output pin di/dt (standard drive)	tdit	25 pF 50 pF	7 8	21 22	52 54	mA/ns

² The typical value of $V_{ox(ac)}$ is expected to be about $0.5 \times NVCC$ and $V_{ox(ac)}$ is expected to track variation in $NVCC$. $V_{ox(ac)}$ indicates the voltage at which the differential output signal must cross. $C_{load} = 25 \text{ pF}$.

Table 24. AC Electrical Characteristics of DDR Type IO Pins in mDDR Mode

Parameter	Symbol	Test Condition	Min. Rise/Fall	Typ.	Max. Rise/Fall	Units
Duty cycle	Fduty	—	45	50	55	%
Clock frequency	f	—	—	133	—	MHz
Output pin slew rate (max. drive)	tps	25 pF 50 pF	0.80/0.92 0.43/0.50	1.35/1.50 0.72/0.81	2.23/2.27 1.66/1.68	V/ns
Output pin slew rate (high drive)	tps	25 pF 50 pF	0.37/0.43 0.19/0.23	0.62/0.70 0.33/0.37	1.03/1.05 0.75/0.77	V/ns
Output pin slew rate (standard drive)	tps	25 pF 50 pF	0.18/0.22 0.10/0.12	0.31/0.35 0.16/0.18	0.51/0.53 0.38/0.39	V/ns
Output pin di/dt (max. drive)	tdit	25 pF 50 pF	64 69	171 183	407 432	mA/ns
Output pin di/dt (high drive)	tdit	25 pF 50 pF	37 39	100 106	232 246	mA/ns
Output pin di/dt (standard drive)	tdit	25 pF 50 pF	18 20	50 52	116 123	mA/ns

Table 25. AC Electrical Characteristics of DDR Type IO Pins in SDRAM Mode

Parameter	Symbol	Test Condition	Min. Rise/Fall	Min. Clock Frequency	Max. Rise/Fall	Units
Clock frequency	f	—	—	125	—	MHz
Output pin slew rate (max. drive)	tps	25 pF 50 pF	1.11/1.20 0.97/0.65	1.74/1.75 0.92/0.94	2.42/2.46 1.39/1.30	V/ns
Output pin slew rate (high drive)	tps	25 pF 50 pF	0.76/0.80 0.40/0.43	1.16/1.19 0.61/0.63	1.76/1.66 0.93/0.87	V/ns
Output pin slew rate (standard drive)	tps	25 pF 50 pF	0.38/0.41 0.20/0.22	0.59/0.60 0.31/0.32	0.89/0.82 0.47/0.43	V/ns
Output pin di/dt (max. drive)	tdit	25 pF 50 pF	89 94	198 209	398 421	mA/ns
Output pin di/dt (high drive)	tdit	25 pF 50 pF	59 62	132 139	265 279	mA/ns
Output pin di/dt (standard drive)	tdit	25 pF 50 pF	29 31	65 69	132 139	mA/ns

NOTE

Test conditions are: pin voltage 1.7 V–1.95 V, capacitance 15 pF for all pins (both DDR and non-DDR pins), drive strength is high (7.2 mA). “High” is defined as 80% of signal value and “low” is defined as 20% of signal value.

SDR SDRAM CLK parameters are measured from the 50% point—that is, “high” is defined as 50% of signal value, and “low” is defined as 50% of signal value. $t_{CH} + t_{CL}$ will not exceed 7.5 ns for 133 MHz. DDR SDRAM CLK parameters are measured at the crossing point of $\overline{SDCLK}$ and $SDCLK$ (inverted clock).

The timing parameters are similar to the ones used in SDRAM data sheets. Table 36 indicates SDRAM requirements. All output signals are driven by the ESDCTL at the negative edge of $SDCLK$, and the parameters are measured at maximum memory frequency.

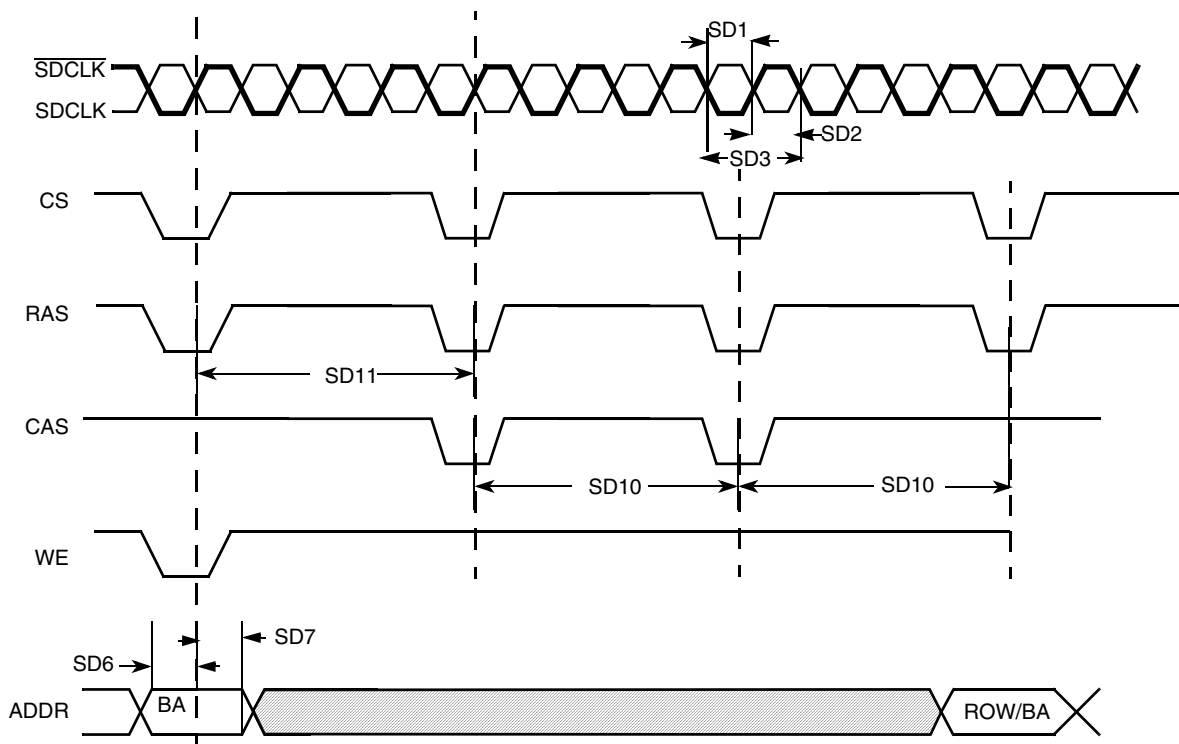


Figure 29. SDRAM Refresh Timing Diagram

Table 37. SDRAM Refresh Timing Parameters

ID	Parameter	Symbol	Min.	Max.	Unit
SD1	SDRAM clock high-level width	t_{CH}	3.4	4.1	ns
SD2	SDRAM clock low-level width	t_{CL}	3.4	4.1	ns
SD3	SDRAM clock cycle time	t_{CK}	7.5	—	ns
SD6	Address setup time	t_{AS}	1.8	—	ns

NOTE

SDRAM CLK and DQS-related parameters are measured from the 50% point—that is, “high” is defined as 50% of signal value and “low” is defined as 50% of signal value.

The timing parameters are similar to the ones used in SDRAM data sheets. Table 44 indicates SDRAM requirements. All output signals are driven by the ESDCTL at the negative edge of SDCLK, and the parameters are measured at maximum memory frequency.

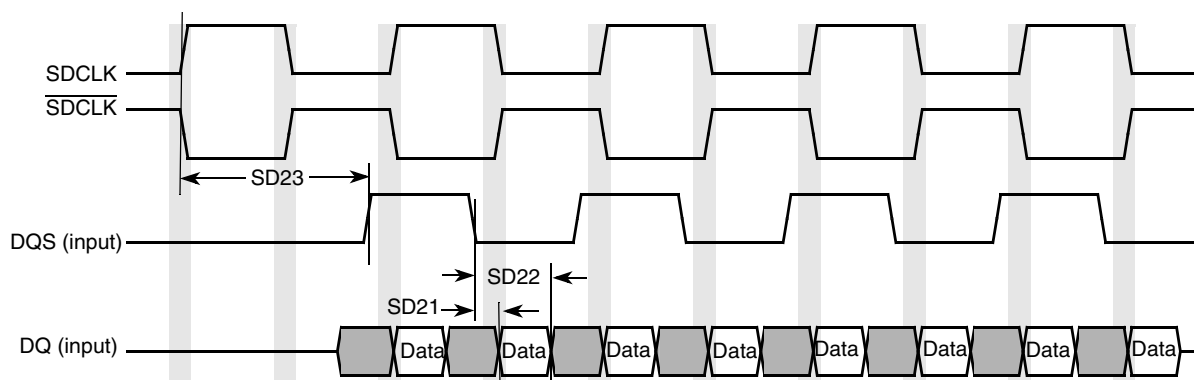


Figure 35. Mobile DDR SDRAM DQ versus DQS and SDCLK Read Cycle Timing Diagram

Table 45. Mobile DDR SDRAM Read Cycle Timing Parameters

ID	Parameter	Symbol	Min.	Max.	Unit
SD21	DQS – DQ Skew (defines the Data valid window in read cycles related to DQS).	tDQSQ	—	0.85	ns
SD22	DQS DQ HOLD time from DQS	tQH	2.3	—	ns
SD23	DQS output access time from SDCLK posedge	tDQSCK	—	6.7	ns

NOTE

SDRAM CLK and DQS-related parameters are measured from the 50% point—that is, “high” is defined as 50% of signal value, and “low” is defined as 50% of signal value.

The timing parameters are similar to the ones used in SDRAM data sheets. Table 45 indicates SDRAM requirements. All output signals are driven by the ESDCTL at the negative edge of SDCLK, and the parameters are measured at maximum memory frequency.

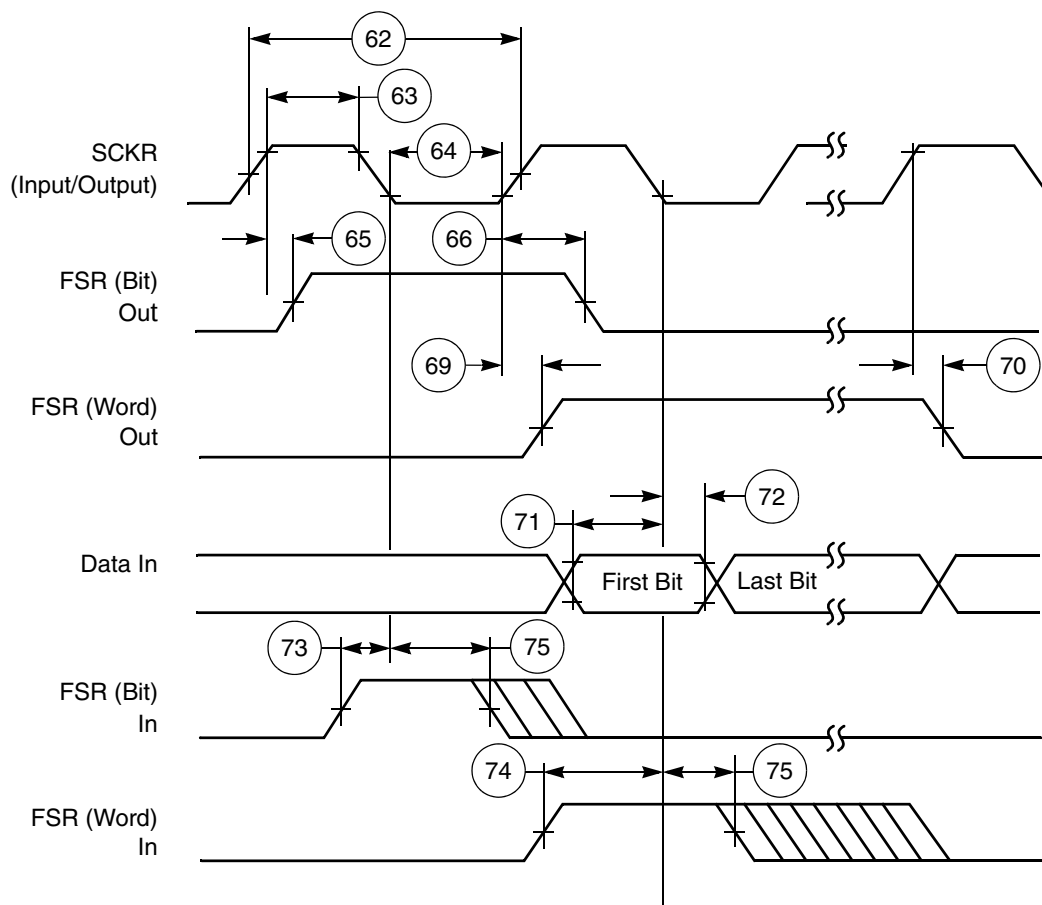


Figure 37. ESDHCv2 Receiver Timing

4.9.7 eSDHCv2 AC Electrical Specifications

Figure 38 depicts the timing of eSDHCv2, and Table 47 lists the eSDHCv2 timing characteristics. The following definitions apply to values and signals described in Table 47:

- LS: low-speed mode. Low-speed card can tolerate a clock up to 400 kHz.
- FS: full-speed mode. For a full-speed MMC card, the card clock can reach 20 MHz; a full-speed SD/SDIO card can reach 25 MHz.
- HS: high-speed mode. For a high-speed MMC card, the card clock can reach 52 MHz; SD/SDIO can reach 50 MHz.

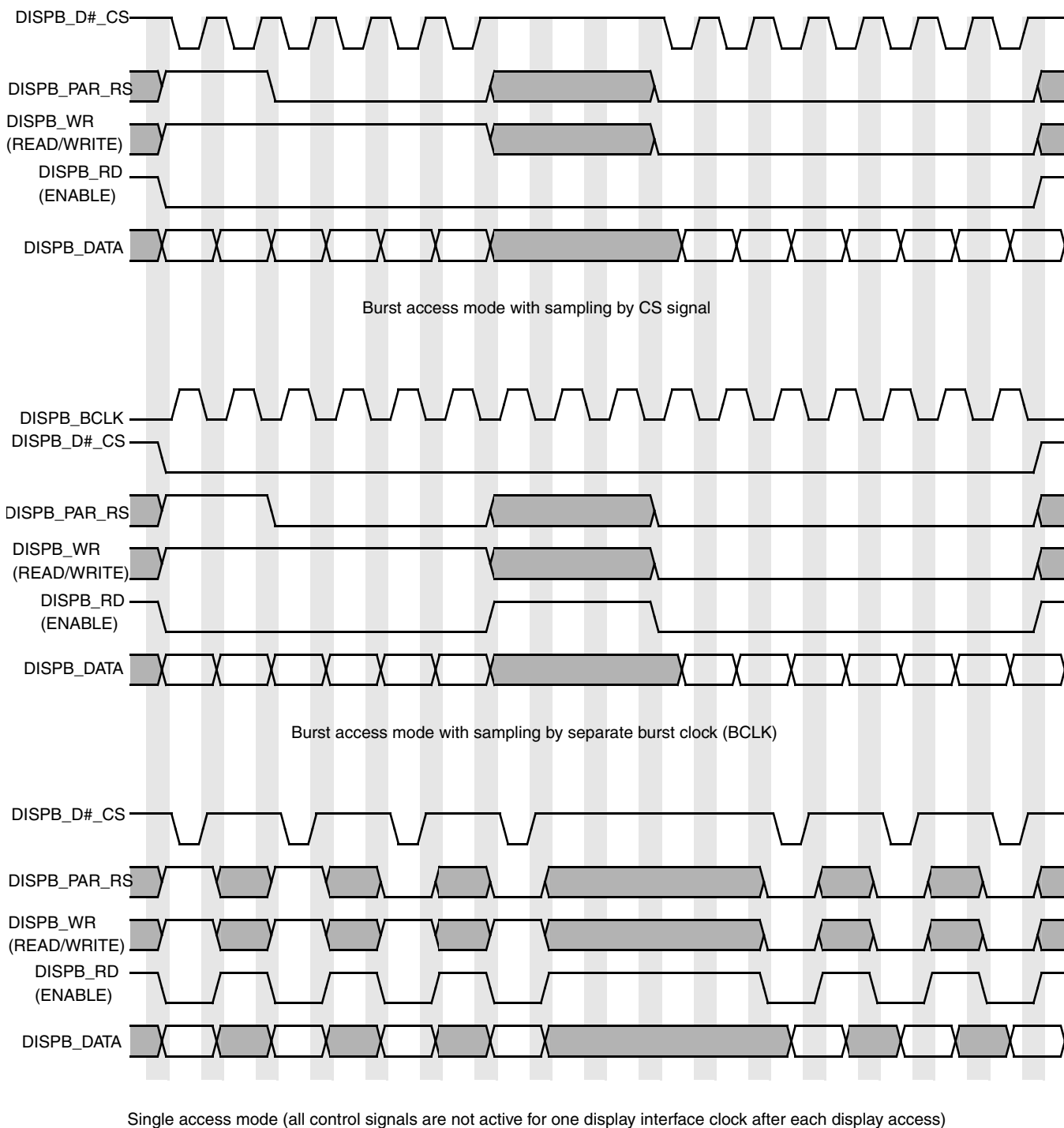


Figure 55. Asynchronous Parallel System 68k Interface (Type 1) Burst Mode Timing Diagram

Table 58. Asynchronous Parallel Interface Timing Parameters—Access Level (continued)

ID	Parameter	Symbol	Min.	Typ. ¹	Max.	Units
IP35	Controls setup time for write	Tdcsw	Tdicuw – 1.5	Tdicuw	—	ns
IP36	Controls hold time for write	Tdchw	Tdicpw – Tdicdw – 1.5	Tdicpw – Tdicdw	—	ns
IP37	Slave device data delay ⁸	Tracc	0	—	Tdrp ⁹ – Tlbd ¹⁰ – Tdicur – 1.5	ns
IP38	Slave device data hold time ⁸	Troh	Tdrp – Tlbd – Tdicdr + 1.5	—	Tdicpr – Tdicdr – 1.5	ns
IP39	Write data setup time	Tds	Tdicdw – 1.5	Tdicdw	—	ns
IP40	Write data hold time	Tdh	Tdicpw – Tdicdw – 1.5	Tdicpw – Tdicdw	—	ns
IP41	Read period ²	Tdicpr	Tdicpr – 1.5	Tdicpr	Tdicpr + 1.5	ns
IP42	Write period ³	Tdicpw	Tdicpw – 1.5	Tdicpw	Tdicpw + 1.5	ns
IP43	Read down time ⁴	Tdicdr	Tdicdr – 1.5	Tdicdr	Tdicdr + 1.5	ns
IP44	Read up time ⁵	Tdicur	Tdicur – 1.5	Tdicur	Tdicur + 1.5	ns
IP45	Write down time ⁶	Tdicdw	Tdicdw – 1.5	Tdicdw	Tdicdw + 1.5	ns
IP46	Write up time ⁷	Tdicuw	Tdicuw – 1.5	Tdicuw	Tdicuw + 1.5	ns
IP47	Read time point ⁹	Tdrp	Tdrp – 1.5	Tdrp	Tdrp + 1.5	ns

¹The exact conditions have not been finalized, but will likely match the current customer requirement for their specific display. These conditions may be device-specific.

² Display interface clock period value for read:

$$T_{dicpr} = T_{HSP_CLK} \cdot \text{ceil} \left[\frac{DISP\#_IF_CLK_PER_RD}{HSP_CLK_PERIOD} \right]$$

³ Display interface clock period value for write:

$$T_{dicpw} = T_{HSP_CLK} \cdot \text{ceil} \left[\frac{DISP\#_IF_CLK_PER_WR}{HSP_CLK_PERIOD} \right]$$

⁴ Display interface clock down time for read:

$$T_{dicdr} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP\#_IF_CLK_DOWN_RD}{HSP_CLK_PERIOD} \right]$$

⁵ Display interface clock up time for read:

$$T_{dicur} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP\#_IF_CLK_UP_RD}{HSP_CLK_PERIOD} \right]$$

⁶ Display interface clock down time for write:

$$T_{dicdw} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP\#_IF_CLK_DOWN_WR}{HSP_CLK_PERIOD} \right]$$

⁷ Display interface clock up time for write:

$$T_{dicuw} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP\#_IF_CLK_UP_WR}{HSP_CLK_PERIOD} \right]$$

⁸ This parameter is a requirement to the display connected to the IPU

⁹ Data read point

$$T_{drp} = T_{HSP_CLK} \cdot \text{ceil} \left[\frac{DISP\#_READ_EN}{HSP_CLK_PERIOD} \right]$$

¹⁰ Loopback delay T_{lbd} is the cumulative propagation delay of read controls and read data. It includes an IPU output delay, a device – level output delay, board delays, a device – level input delay, an IPU input delay. This value is device specific.

The following parameters are programmed via the DI_DISP#_TIME_CONF_1, DI_DISP#_TIME_CONF_2, and DI_HSP_CLK_PER registers:

- DISP#_IF_CLK_PER_WR, DISP#_IF_CLK_PER_RD
- HSP_CLK_PERIOD
- DISP#_IF_CLK_DOWN_WR
- DISP#_IF_CLK_UP_WR
- DISP#_IF_CLK_DOWN_RD
- DISP#_IF_CLK_UP_RD
- DISP#_READ_EN

4.9.13.5 Serial Interfaces, Functional Description

The IPU supports the following types of asynchronous serial interfaces:

- 3-wire (with bidirectional data line)
- 4-wire (with separate data input and output lines)
- 5-wire type 1 (with sampling RS by the serial clock)
- 5-wire type 2 (with sampling RS by the chip select signal)

Figure 62 depicts timing of the 3-wire serial interface. The timing images correspond to active-low $DISPB_D\#_CS$ signal and the straight polarity of the $DISPB_SD_D_CLK$ signal.

For this interface, a bidirectional data line is used outside the device. The IPU still uses separate input and output data lines ($IPP_IND_DISPB_SD_D$ and $IPP_DO_DISPB_SD_D$). The I/O mux connects the internal data lines to the bidirectional external line according to the $IPP_OBE_DISPB_SD_D$ signal provided by the IPU.

Each data transfer can be preceded by an optional preamble with programmable length and contents. The preamble is followed by read/write (RW) and address (RS) bits. The order of these bits is programmable. The RW bit can be disabled. The following data can consist of one word or of a whole burst. The interface parameters are controlled by the $DI_SER_DISPn_CONF$ registers ($n = 1, 2$).

4.9.13.5.10 Serial Interfaces, Electrical Characteristics

Figure 66 depicts timing of the serial interface. Table 59 lists the timing parameters at display access level.

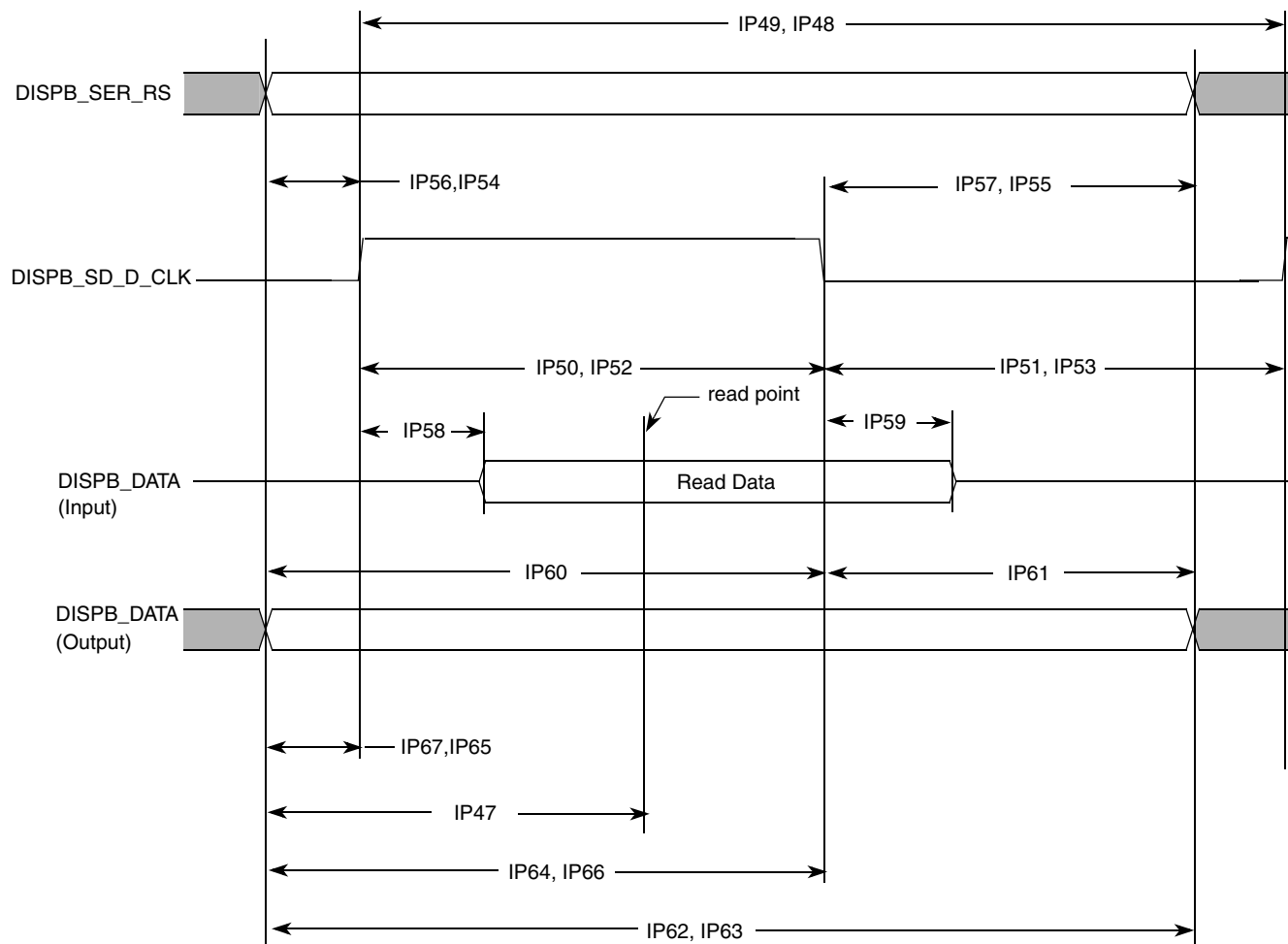


Figure 66. Asynchronous Serial Interface Timing Diagram

Table 59. Asynchronous Serial Interface Timing Parameters—Access Level

ID	Parameter	Symbol	Min.	Typ. ¹	Max.	Units
IP48	Read system cycle time	Tcycr	Tdicpr – 1.5	Tdicpr ²	Tdicpr + 1.5	ns
IP49	Write system cycle time	Tcycw	Tdicpw – 1.5	Tdicpw ³	Tdicpw + 1.5	ns
IP50	Read clock low pulse width	Trl	Tdicdr – Tdicur – 1.5	Tdicdr ⁴ – Tdicur ⁵	Tdicdr – Tdicur + 1.5	ns
IP51	Read clock high pulse width	Trh	Tdicpr – Tdicdr + Tdicur – 1.5	Tdicpr – Tdicdr + Tdicur	Tdicpr – Tdicdr + Tdicur + 1.5	ns
IP52	Write clock low pulse width	Twl	Tdicdw – Tdicuw – 1.5	Tdicdw ⁶ – Tdicuw ⁷	Tdicdw – Tdicuw + 1.5	ns
IP53	Write clock high pulse width	Twh	Tdicpw – Tdicdw + Tdicuw – 1.5	Tdicpw – Tdicdw + Tdicuw	Tdicpw – Tdicdw + Tdicuw + 1.5	ns
IP54	Controls setup time for read	Tdcscr	Tdicur – 1.5	Tdicur	—	ns

Table 59. Asynchronous Serial Interface Timing Parameters—Access Level (continued)

ID	Parameter	Symbol	Min.	Typ. ¹	Max.	Units
IP55	Controls hold time for read	Tdchr	Tdicpr – Tdicdr – 1.5	Tdicpr – Tdicdr	—	ns
IP56	Controls setup time for write	Tdcsw	Tdicuw – 1.5	Tdicuw	—	ns
IP57	Controls hold time for write	Tdchwr	Tdicpw – Tdicdw – 1.5	Tdicpw – Tdicdw	—	ns
IP58	Slave device data delay ⁸	Tracc	0	—	Tdrp ⁹ – Tlbd ¹⁰ – Tdicur – 1.5	ns
IP59	Slave device data hold time ⁸	Troh	Tdrp – Tlbd – Tdicdr + 1.5	—	Tdicpr – Tdicdr – 1.5	ns
IP60	Write data setup time	Tds	Tdicdw – 1.5	Tdicdw	—	ns
IP61	Write data hold time	Tdh	Tdicpw – Tdicdw – 1.5	Tdicpw – Tdicdw	—	ns
IP62	Read period ²	Tdicpr	Tdicpr – 1.5	Tdicpr	Tdicpr + 1.5	ns
IP63	Write period ³	Tdicpw	Tdicpw – 1.5	Tdicpw	Tdicpw + 1.5	ns
IP64	Read down time ⁴	Tdicdr	Tdicdr – 1.5	Tdicdr	Tdicdr + 1.5	ns
IP65	Read up time ⁵	Tdicur	Tdicur – 1.5	Tdicur	Tdicur + 1.5	ns
IP66	Write down time ⁶	Tdicdw	Tdicdw – 1.5	Tdicdw	Tdicdw + 1.5	ns
IP67	Write up time ⁷	Tdicuw	Tdicuw – 1.5	Tdicuw	Tdicuw + 1.5	ns
IP68	Read time point ⁹	Tdrp	Tdrp – 1.5	Tdrp	Tdrp + 1.5	ns

¹ The exact conditions have not been finalized, but will likely match the current customer requirement for their specific display. These conditions may be device specific.

² Display interface clock period value for read:

$$T_{dicpr} = T_{HSP_CLK} \cdot \text{ceil} \left[\frac{DISP_IF_CLK_PER_RD}{HSP_CLK_PERIOD} \right]$$

³ Display interface clock period value for write:

$$T_{dicpw} = T_{HSP_CLK} \cdot \text{ceil} \left[\frac{DISP_IF_CLK_PER_WR}{HSP_CLK_PERIOD} \right]$$

⁴ Display interface clock down time for read:

$$T_{dicdr} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP_IF_CLK_DOWN_RD}{HSP_CLK_PERIOD} \right]$$

⁵ Display interface clock up time for read:

$$T_{dicur} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP_IF_CLK_UP_RD}{HSP_CLK_PERIOD} \right]$$

⁶ Display interface clock down time for write:

$$T_{dicdw} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP_IF_CLK_DOWN_WR}{HSP_CLK_PERIOD} \right]$$

⁷ Display interface clock up time for write:

$$T_{dicuw} = \frac{1}{2} T_{HSP_CLK} \cdot \text{ceil} \left[\frac{2 \cdot DISP_IF_CLK_UP_WR}{HSP_CLK_PERIOD} \right]$$

⁸ This parameter is a requirement to the display connected to the IPU.

4.9.22.4 SSI Receiver Timing with External Clock

Figure 95 depicts the SSI receiver timing with external clock, and Table 81 lists the timing parameters.

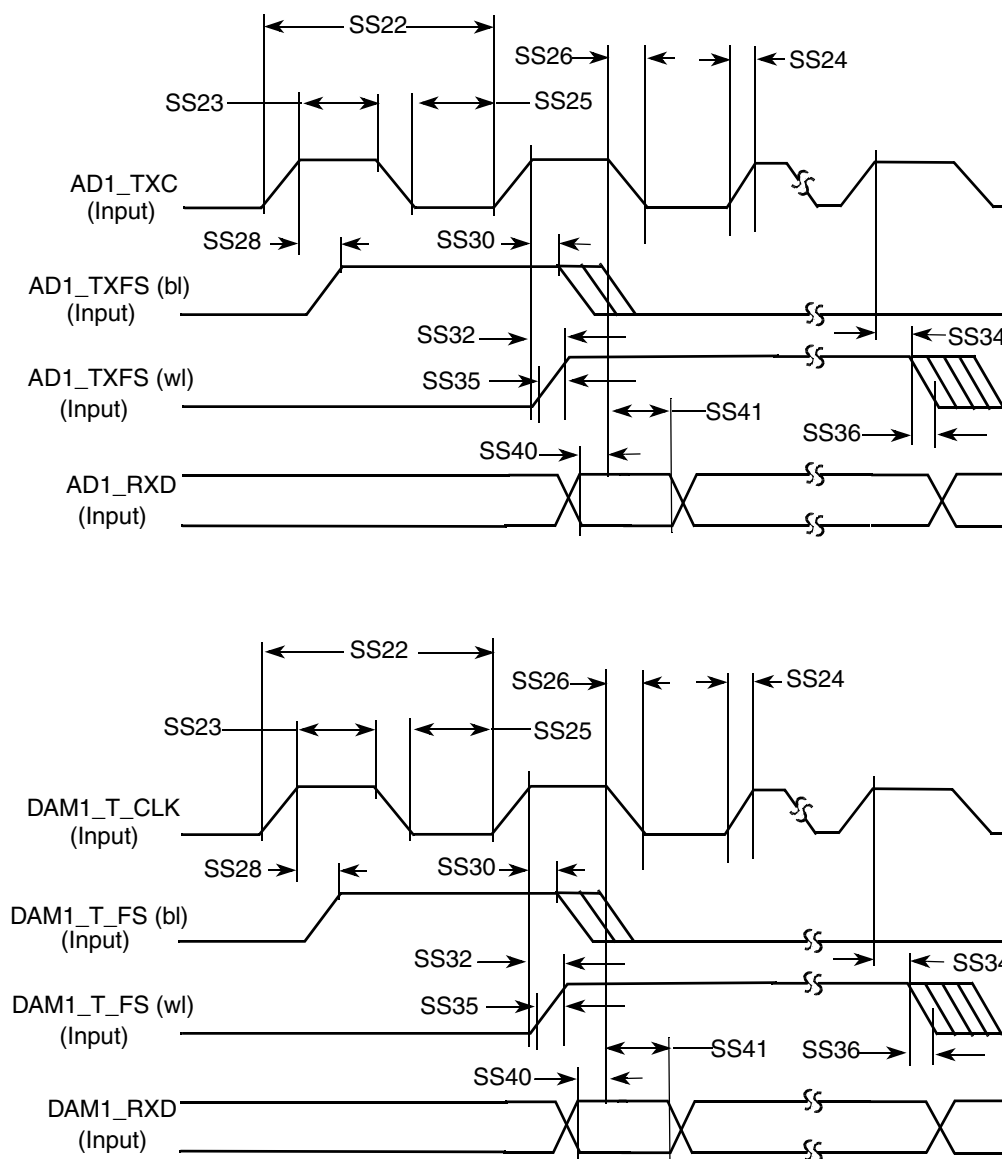


Figure 95. SSI Receiver with External Clock Timing Diagram

Table 81. SSI Receiver with External Clock Timing Parameters

ID	Parameter	Min.	Max.	Unit
External Clock Operation				
SS22	(Tx/Rx) CK clock period	81.4	—	ns
SS23	(Tx/Rx) CK clock high period	36.0	—	ns
SS24	(Tx/Rx) CK clock rise time	—	6.0	ns

Table 95. Silicon Revision 2.1 Signal Ball Map Locations

Signal ID	Ball Location	Signal ID	Ball Location
A0	A5	ATA_DATA7	Y3
A1	D7	ATA_DATA8	U4
A10	F15	ATA_DATA9	W3
A11	D5	ATA_DIOR	Y6
A12	F6	ATA_DIOW	W6
A13	B3	ATA_DMACK	V6
A14	D14	ATA_DMARQ	T3
A15	D15	ATA_INTRQ	V2
A16	D13	ATA_IORDY	U6
A18	D12	ATA_RESET_B	T6
SDQS1	E11	SDQS0	E14
A19	D11	BOOT_MODE0	W10
A2	E7	BOOT_MODE1	U9
A21	D10	CAPTURE	V12
SDQS2	E10	RAS	E16
A22	D9	CLK_MODE0	Y10
SDQS3	E9	CLK_MODE1	T10
A24	D8	CLKO	V10
A25	E8	COMPARE	T12
A3	C6	CONTRAST	L16
A4	D6	CS0	F17
A5	B5	CS1	E19
A6	C5	CS2	B20
A7	A4	CS3	C19
A8	B4	CS4	E18
A9	A3	CS5	F19
ATA_BUFF_EN ¹	T5	CSI_D10	V16
ATA_CS0	V7	CSI_D11	T15
ATA_CS1	T7	CSI_D12	W16
ATA_DA0	R4	CSI_D13	V15
ATA_DA1	V1	CSI_D14	U14
ATA_DA2	R5	CSI_D15	Y16
ATA_DATA0	Y5	CSI_D8	U15
ATA_DATA1	W5	CSI_D9	W17
ATA_DATA10	V3	CSI_HSYNC	V14
ATA_DATA11	Y2	CSI_MCLK	W15
ATA_DATA12	U3	CSI_PIXCLK	Y15
ATA_DATA13	W2	CSI_VSYNC	T14
ATA_DATA14	W1	CSPI1_MISO	V9
ATA_DATA15	T4	CSPI1_MOSI	W9
ATA_DATA2	V5	CSPI1_SCLK	W8
ATA_DATA3	U5	CSPI1_SPI_RDY	T8
ATA_DATA4	Y4	CSPI1_SS0	Y8
ATA_DATA5	W4	CSPI1_SS1	U8
ATA_DATA6	V4	CTS1	R3

Table 95. Silicon Revision 2.1 Signal Ball Map Locations (continued)

Signal ID	Ball Location	Signal ID	Ball Location
SD1_CLK	V18	SDCLK	E12
SD1_CMD	Y19	SDCLK_B	E13
SD1_DATA0	R14	SD0	B17
SD1_DATA1	U16	SD15	A13
SD1_DATA2	W18	SD23	A10
SD1_DATA3	V17	A23	C7
SD10	A15	SDWE	G15
SD11	B15	SJC_MOD	U17
A17	C13	SRXD4	L1
SD13	B14	SRXD5	K4
SD14	A14	STXD4	M2
SD12	B13	STXD5	K1
SD16	C12	STXFS4	L2
SD17	C11	STXFS5	J6
SD18	A12	TCK	R17
SD19	B12	TDI	P15
SD2	B18	TDO	R15
SD2_CLK	W14	TEST_MODE	Y7
SD2_CMD	U13	TMS	R16
SD2_DATA0	V13	TRSTB	T16
SD2_DATA1	T13	TTM_PIN	M16
SD2_DATA2	Y14	TX0	G4
SD2_DATA3	U12	TX1	H1
SD20	B11	TX2_RX3	H5
SD21	A11	TX3_RX2	J2
A20	C10	TX4_RX1	H4
SD22	B10	TX5_RX0	J3
SD24	A9	TXD1	R6
SD25	C9	TXD2	H2
SD26	B9	USBOTG_OC	U7
SD27	A8	USBOTG_PWR	W7
SD28	B8	USBPHY1_DM	N19
SD29	C8	USBPHY1_DP	P19
SD3	C16	USBPHY1_RREF	R19
SD30	A7	USBPHY1_UID	N18
SD31	B7	USBPHY1_UPLLGN	N14
SD4	A18	USBPHY1_UPLLVDD	N15
SD5	C15	USBPHY1_UPLLVDD	P17
SD6	A17	USBPHY1_VBUS	P18
SD7	B16	USBPHY1_VDDA_BIAS	R20
SD8	C14	USBPHY1_VSSA_BIAS	R18
SD9	A16	USBPHY2_DM	Y17
SDBA0	A6	USBPHY2_DP	Y18
SDBA1	B6	VDD	M6
SDCKE0	D18	VDD	F7
CAS	E17	VDD	J7

Table 95. Silicon Revision 2.1 Signal Ball Map Locations (continued)

Signal ID	Ball Location	Signal ID	Ball Location
VDD	L7	VSS	L9
VDD	N7	VSS	N9
VDD	R7	VSS	K10
VDD	F8	VSS	P10
VDD	R8	VSS	H11
VDD	F9	VSS	H12
VDD	F12	NVCC_EMI2	H13
VDD	R12	VSS	J13
VDD	G13	VSS	K13
VDD	H15	VSS	L13
VDD	J15	VSS	T17
VSS	A1	VSS	A20
VSS	Y1	VSS	Y20
VSS	J8	VSTBY	T9
VSS	M8	WDOG_RST	Y12
VSS	N8	XTAL_AUDIO	V19
VSS	J9	XTAL24M	U20

¹ Not available for the MCIMX351.

Table 96. Silicon Revision 2.0 Ball Map—17 x 17, 0.8 mm Pitch¹

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	
A	VSS	D0	A9	A7	A0	SDB A0	SD3 0	SD2 7	SD2 4	SDQ S2	SD2 1	SD1 8	SDQ S1	SD1 4	SD1 0	SD9	SD6	SD4	SD1	VSS	A
B	D5	D2	A13	A8	A5	SDB A1	SD3 1	SD2 8	SD2 6	SD2 3	SD2 0	SD1 9	SD1 5	SD1 3	SD1 1	SD7	SDQ S0	SD2	DQM 0	CS2	B
C	D8	D7	D4	MA1 0	A6	A3	SDQ S3	SD2 9	SD2 5	SD2 2	SD1 7	SD1 6	SD1 2	SD8	SD5	SD3	SD0	DQM 3	CS3	RW	C
D	D14	D10	D6	D1	A11	A4	A1	A24	A22	A20	A19	A17	A16	A14	A15	DQM 2	DQM 1	SDC KE0	ECB	LBA	D
E	NFC LE	D15	D12	D9	D3	D11	A2	A25	A23	A21	A18	SDC LK	SDC LK_ B	BCL K	RAS	CAS	SDC KE1	CS4	CS1	OE	E
F	NFR E_B	NFA LE	NFR B	NFW P_B	D13	A12	VDD	VDD	VDD	NVC C_E MI1	NVC C_E MI1	VDD	NVC C_E MI2	NVC C_E MI2	A10	EB1	CS0	EB0	CS5	LD0	F
G	RTS 2	NFW E_B	NF_ CE0	TX0	CTS 2	NVC C_N FC	NVC C_E MI1	NVC C_E MI1	NVC C_E MI1	NVC C_E MI1	NVC C_E MI1	NVC C_E MI2	VDD	NVC C_E MI3	SDW E	LD3	LD2	LD1	LD4	LD7	G
H	TX1	TXD 2	RXD 2	TX4_ RX1	TX2_ RX3	NVC C_N FC	NVC C_N FC	NGN D_E MI1	NVC C_E MI1	NGN D_E MI1	VSS	VSS	VSS	NVC C_L CDC	VDD	LD5	LD8	LD6	LD9	LD10	H
J	FST	TX3_ RX2	TX5_ RX0	SCK T	HCK T	STX FS5	VDD	VSS	VSS	NGN D_E MI1	NGN D_E MI2	NGN D_E MI3	VSS	NVC C_L CDC	VDD	LD12	LD14	LD11	LD13	LD15	J
K	STX D5	HCK R	SCK R	SRX D5	FSR	NVC C_MI SC	NVC C_MI SC	NGN D_MI SC	NGN D_N FC	VSS	NGN D_L CDC	NGN D_E MI3	VSS	LD16	LD22	LD20	LD21	LD18	LD17	LD19	K
L	SRX D4	STX FS4	I2C2_ CL K	SCK 4	SCK 5	FEC _TD ATA3	VDD	NVC C_MI SC	VSS	NGN D_A TA	NGN D_C RM	NGN D_L CDC	VSS	NVC C_L CDC	D3_ FPS HIFT	CON TRA ST	D3_ CLS	D3_ HSY NC	LD23	D3_ DRD Y	L
M	I2C2_ _DAT	STX D4	FEC _RD ATA2	FEC _TD ATA1	FEC _TD ATA2	VDD	NGN D_MI SC	VSS	NGN D_A TA	NGN D_M LB	FUS E_V SS	PGN D	NGN D_JT AG	NVC C_L CDC	PHY 1_V DDA	TTM _PIN	D3_ REV	D3_ SPL	D3_ VSY NC	I2C1_ _CL K	M
N	FEC _RD ATA3	FEC _RD ATA1	FEC _RX_ _ER R	FEC _TX_ _ERR	FEC _CR S	NVC C_A TA	VDD	VSS	VSS	NGN D_C SI	MGN D	NGN D_S DIO	PVD D	USB PHY 1_U PLL GND	USB PHY 1_U PLL VDD	PHY 1_V SSA	I2C1_ _DAT	USB PHY 1_UI D	USB PHY 1_D M	PHY 1_V DDA	N
P	FEC _MDI O	FEC _RD ATA0	FEC _CO L	FEC _TX_ _CLK	FEC _TD ATA0	NVC C_A TA	NVC C_A TA	NVC C_A TA	NGN D_A TA	VSS	MVD D	PHY 2_V SS	FUS E_V DD	NVC C_S DIO	TDI	NVC C_JT AG	USB PHY 1_U PLL VDD	USB PHY 1_V BUS	USB PHY 1_D P	PHY 1_V SSA	P
R	FEC _MD C	FEC _RX_ _CL K	CTS 1	ATA_ DA0	ATA_ DA2	TXD 1	VDD	VDD	NVC C_C RM	NVC C_M LB	NVC C_C SI	VDD	PHY 2_V DD	SD1_ _DAT A0	TDO	TMS	TCK	USB PHY 1_V SSA_ _BIA S	USB PHY 1_R REF	USB PHY 1_V DDA_ _BIA S	R
T	FEC _TX_ _EN	FEC _RX_ _DV	ATA_ DMA RQ	ATA_ DATA 15	ATA_ BUF F_E N	ATA_ RES ET_ B	ATA_ CS1	CSPI 1_S PI_ R DY	VST BY	CLK _MO DE1	GPI O1_ 0	COM PAR E	SD2_ _DAT A1	CS1_ _VSY NC	CS1_ _D11	TRS TB	VSS	OSC 24M _VS S	OSC 24M _VD D	EXT AL24 M	T
U	RTS 1	RXD 1	ATA_ DATA 12	ATA_ DATA 8	ATA_ DATA 3	ATA_ IOR DY	USB OTG _OC	CSPI 1_S S1	BOO T_M ODE 1	RES ET_ I N_ B	GPI O2_ 0	SD2_ _DAT A3	SD2_ _CM D	CS1_ _D14	CS1_ _D8	SD1_ _DAT A1	SJC _MO D	RTC K	OSC _AU DIO_ VSS	XTAL 24M	U